

**Silicon Standard  
Recovery Diode**
 $V_{RRM} = 200\text{ V} - 1000\text{ V}$   
 $I_F = 150\text{ A}$ 
**Features**

- High Surge Capability
- Types up to 1000 V  $V_{RRM}$

**DO-8 Package**

**Maximum ratings, at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified ("R" devices have leads reversed)**

Parameter	Symbol	Conditions	150K(R)20A	150K(R)40A	150K(R)60A	150K(R)80A	150K(R)100A	Unit
Repetitive peak reverse voltage	$V_{RRM}$		200	400	600	800	1000	V
DC blocking voltage	$V_{DC}$		200	400	600	800	1000	V
Continuous forward current	$I_F$	$T_C \leq 110\text{ }^\circ\text{C}$	150	150	150	150	150	A
Surge non-repetitive forward current, Half Sine Wave	$I_{FSM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 8.3\text{ ms}$	3740	3740	3740	3740	3740	A
$I_{F1}$ for fusing	$I_{F1}$	$t = 8.3\text{ms}$	58000	58000	58000	58000	58000	$\text{A}^2\text{sec}$
Operating temperature	$T_J$		-40 to 200	-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-40 to 200	-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$

**Electrical characteristics, at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	150K(R)20A	150K(R)40A	150K(R)60A	150K(R)80A	150K(R)100A	Unit
Diode forward voltage	$V_F$	$I_F = 150\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	1.33	1.33	1.33	1.33	1.33	V
Reverse current	$I_R$	$V_R = V_{RRM}$ , $T_J = 175\text{ }^\circ\text{C}$	35	35	35	32	24	mA

**Thermal characteristics**

Thermal resistance, junction - case	$R_{\theta JC}$		0.25	0.25	0.25	0.25	0.25	$^\circ\text{C/W}$
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